Octal Bus Buffer/Line Driver Inverting with 3-State Outputs

The MC74VHC240 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC240 is an inverting 3-state buffer, and has two active-low output enables. This device is designed to drive bus lines or buffer memory address registers.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: $t_{PD} = 3.6 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 120 FETs or 30 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

_			
OEA [1●	20] v _{cc}
A1 [2	19	OEB
<u>YB4</u> [3	18] <u>YA1</u>
A2 [4	17] B4
<u>YB3</u> [5	16] YA2
A3 [6	15] B3
YB2	7	14] YA3
A4 [8	13] B2
YB1 [9	12	YA4
GND [10	11] B1

Figure 1. Pin Assignment



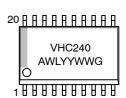
ON Semiconductor™

http://onsemi.com

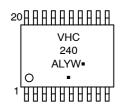
MARKING DIAGRAMS



SOIC-20 DW SUFFIX CASE 751D







VHC240 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC240DWR2G	SOIC-20	1000 Units/Reel
MC74VHC240DTR2G	TSSOP-20	2500 Units/Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

FUNCTION TABLE

INPL	JTS	OUTPUTS
OEA, OEB A, B		YA, YB
L	L	Н
L	Н	L
Н	X	Z

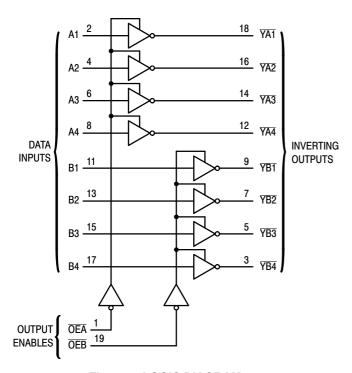


Figure 1. LOGIC DIAGRAM

MAXIMUM RATINGS*

Symbol	Parameter	Parameter		
V _{CC}	DC Supply Voltage	- 0.5 to + 7.0	V	
V _{in}	DC Input Voltage	- 0.5 to + 7.0	V	
V _{out}	DC Output Voltage	$-$ 0.5 to V $_{\rm CC}$ + 0.5	V	
I _{IK}	Input Diode Current	- 20	mA	
I _{OK}	Output Diode Current	± 20	mA	
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GN	± 75	mA	
P _D	Power Dissipation in Still Air,	ower Dissipation in Still Air, SOIC Packages† TSSOP Package†		mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage			5.5	٧
V _{in}	DC Input Voltage			5.5	٧
V _{out}	DC Output Voltage			V_{CC}	٧
T _A	Operating Temperature, All Package Types			+ 85	°C
t _r , t _f		$V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	0	100 20	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

[†]Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

DC ELECTRICAL CHARACTERISTICS

			Vcc		T _A = 25°C		$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -4\text{mA} \\ I_{OH} &= -8\text{mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μА
I _{OZ}	Maximum Three-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μА
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

					T _A = 25°C		T _A = - 40	0 to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or B to YB	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		5.3 7.8	7.5 11.0	1.0 1.0	9.0 12.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		3.6 5.1	5.5 7.5	1.0 1.0	6.5 8.5	
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or OEB to YB	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	$C_L = 15pF$ $C_L = 50pF$		6.6 9.1	10.6 14.1	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$			4.7 6.2	7.3 9.3	1.0 1.0	8.5 10.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OEA to YA or OEB to YB	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C _L = 50pF		10.3	14.0	1.0	16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C _L = 50pF		6.7	9.2	1.0	10.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 3.3 ± 0.3V (Note 1.)	C _L = 50pF			1.5		1.5	ns
		V _{CC} = 5.0 ± 0.5V (Note 1.)	C _L = 50pF			1.0		1.0	
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)				6				pF

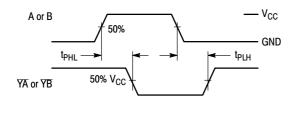
		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 2.)	17	рF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter		Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}		0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}		- 0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS



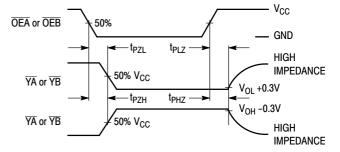
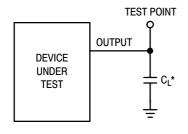
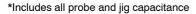


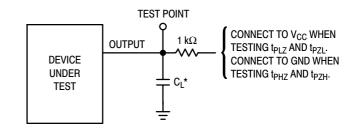
Figure 2.

Figure 3.

TEST CIRCUITS







*Includes all probe and jig capacitance

Figure 4. Test Circuit

Figure 5. Test Circuit

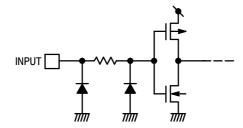
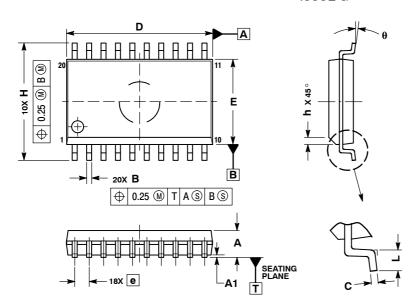


Figure 6. Input Equivalent Circuit

PACKAGE DIMENSIONS

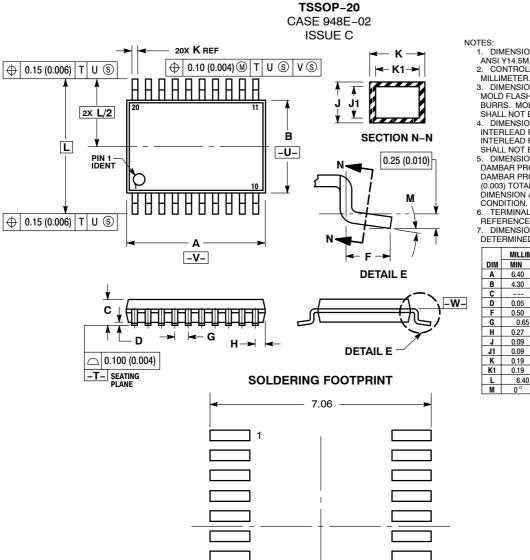
SOIC-20 CASE 751D-05 ISSUE G



- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN MAX			
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
C	0.23	0.32		
D	12.65	12.95		
Е	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION:
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE
- MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBALE PROTRUSION ALLOWARE E
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
C	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007 0.010	
٦	6.40 BSC		0.252	BSC
M	0°	8°	0°	8°

0.65 **PITCH**

DIMENSIONS: MILLIMETERS

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ite (SCILLC) as Solitude services are injected in the chargest without further holice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

16X 1.26

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

16X 0.36

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative